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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

TAKAFUJI et al

Serial No. 10/802,735

Filed: March 18, 2004



Atty. Ref.: 1035-501

Group: 2811

Examiner:

For: SEMICONDUCTOR DEVICE AND METHOD OF
MANUFACTURING THE SAME

* * * * *

Commissioner for Patents
 P. O. Box 1450
 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

- All listed documents are attached.
- This application was filed after June 30, 2003 so that copies of U.S. Patent Publications are not required and are not attached.
- Listed foreign patent publications and other documents are enclosed.
- The partial translations were provided to the undersigned by the applicants' foreign representative. The undersigned has no knowledge regarding the pertinency of the partially translated portions vis-á-vis the document as a whole. The partial translations are merely provided for whatever convenience they may be.
- The listed documents were cited in the ISR and copies should have been supplied by WIPO directly to the US PTO. If copies are not timely received from WIPO, please telephone the undersigned so that copies can be timely supplied for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

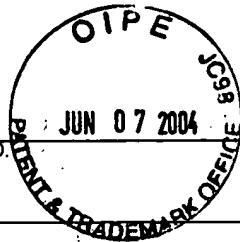
Respectfully submitted,
NIXON & VANDERHYE P.C.

June 7, 2004

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~~ATTY. DOCKET NO.~~

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INFORMATION DISCLOSURE CITATION

1035-501
APPLICANT

10/802,735

(Use several sheets if necessary)

TAKAFUJI et al

FILING DATE

GROUP

March 18, 2004

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

TRANSLATION

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	Salerno et al, "Single Crystal Silicon AMLCDs", Conference Record of the 1994 International Display Research Conference (IDRC) (1994), pp. 39-44
	Tong et al, "Semiconductor Wafer Bonding: Science and Technology", John Wiley & Sons, Inc., New York, 1999, pp. 8-11, 488-55, 58-65, 108 and 109
	Warner et al, "Low-Temperature Oxide-Bonded Three-Dimensional Integrated Circuits", 2002 IEEE International SOI Conference, October 2002, pp. 123-125
	Allen et al, "SOI Uniformity and Surface Smoothness Improvement Using GCIB Processing", 2002 IEEE International SOI Conference, October 2002, pp. 192-193
	Matsumoto et al, "70 nm SOI-CMOS of 135 GHz f_{\max} with Dual Offset-Implanted Source-Drain Extension Structure for RF/Analog and Logic Applications", International Electron Device Meeting, December 2001, pp. 219-222
	Vandooren et al, "Scaling Assessment of Fully-Depleted SOI Technology at the 30nm Gate Length Generation", 2002 IEEE International SOI Conference Proceedings, October 2002, pp. 25-27

*Examiner _____ Date Considered _____

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.